

Fariba Hatami

List of Publications by Year in descending order

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79
papers

3,479
citations

236925

25
h-index

133252

59
g-index

79
all docs

79
docs citations

79
times ranked

4790
citing authors

#	ARTICLE	IF	CITATIONS
1	Monolayer semiconductor nanocavity lasers with ultralow thresholds. <i>Nature</i> , 2015, 520, 69-72.	27.8	713
2	Radiative recombination in type-II GaSb/GaAs quantum dots. <i>Applied Physics Letters</i> , 1995, 67, 656-658.	3.3	313
3	Deterministic Coupling of a Single Nitrogen Vacancy Center to a Photonic Crystal Cavity. <i>Nano Letters</i> , 2010, 10, 3922-3926.	9.1	309
4	Strong Enhancement of Light-Matter Interaction in Graphene Coupled to a Photonic Crystal Nanocavity. <i>Nano Letters</i> , 2012, 12, 5626-5631.	9.1	248
5	Carrier dynamics in type-II GaSb/GaAs quantum dots. <i>Physical Review B</i> , 1998, 57, 4635-4641.	3.2	231
6	Controlling the spontaneous emission rate of monolayer MoS ₂ in a photonic crystal nanocavity. <i>Applied Physics Letters</i> , 2013, 103, 181119.	3.3	194
7	Second harmonic generation in gallium phosphide photonic crystal nanocavities with ultralow continuous wave pump power. <i>Optics Express</i> , 2009, 17, 22609.	3.4	147
8	Control of two-dimensional excitonic light emission via photonic crystal. <i>2D Materials</i> , 2014, 1, 011001.	4.4	144
9	Biomedical terahertz imaging with a quantum cascade laser. <i>Applied Physics Letters</i> , 2006, 88, 153903.	3.3	133
10	Nanocavity Integrated van der Waals Heterostructure Light-Emitting Tunneling Diode. <i>Nano Letters</i> , 2017, 17, 200-205.	9.1	129
11	A high-resolution spectrometer based on a compact planar two dimensional photonic crystal cavity array. <i>Applied Physics Letters</i> , 2012, 100, 231104.	3.3	73
12	Efficient Extraction of Zero-Phonon-Line Photons from Single Nitrogen-Vacancy Centers in an Integrated GaP-on-Diamond Platform. <i>Physical Review Applied</i> , 2016, 6, .	3.8	64
13	400%/W second harmonic conversion efficiency in 14 μ m-diameter gallium phosphide-on-oxide resonators. <i>Optics Express</i> , 2018, 26, 33687.	3.4	47
14	Second harmonic generation in GaP photonic crystal waveguides. <i>Applied Physics Letters</i> , 2011, 98, 263113.	3.3	44
15	Planar ordering of InP quantum dots on (1 0 0)In _{0.48} Ga _{0.52} P. <i>Journal of Crystal Growth</i> , 2000, 216, 26-32.	1.5	39
16	Radiative recombination from InP quantum dots on (100) GaP. <i>Applied Physics Letters</i> , 2001, 78, 2163-2165.	3.3	35
17	InSb and InSb:N multiple quantum dots. <i>Applied Physics Letters</i> , 2006, 89, 133115.	3.3	34
18	Frequency Control of Single Quantum Emitters in Integrated Photonic Circuits. <i>Nano Letters</i> , 2018, 18, 1175-1179.	9.1	34

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19	Photoluminescence sensitivity to methanol vapours of surface InP quantum dot: Effect of dot size and coverage. <i>Sensors and Actuators B: Chemical</i> , 2013, 189, 113-117.	7.8	31
20	Single-dot optical emission from ultralow density well-isolated InP quantum dots. <i>Applied Physics Letters</i> , 2008, 93, 143111.	3.3	30
21	Vapour sensing properties of InP quantum dot luminescence. <i>Sensors and Actuators B: Chemical</i> , 2012, 162, 149-152.	7.8	29
22	Large-scale GaP-on-diamond integrated photonics platform for NV center-based quantum information. <i>Journal of the Optical Society of America B: Optical Physics</i> , 2016, 33, B35.	2.1	29
23	Sum-frequency generation in doubly resonant GaP photonic crystal nanocavities. <i>Applied Physics Letters</i> , 2010, 97, 043103.	3.3	28
24	Inverse-designed photon extractors for optically addressable defect qubits. <i>Optica</i> , 2020, 7, 1805.	9.3	28
25	Tunable-wavelength second harmonic generation from GaP photonic crystal cavities coupled to fiber tapers. <i>Optics Express</i> , 2010, 18, 12176.	3.4	27
26	Lithographic positioning of fluorescent molecules on high-Q photonic crystal cavities. <i>Applied Physics Letters</i> , 2009, 95, 123113.	3.3	26
27	Selective Epitaxy of InP on Si and Rectification in Graphene/InP/Si Hybrid Structure. <i>ACS Applied Materials & Interfaces</i> , 2016, 8, 26948-26955.	8.0	23
28	InP quantum dots in GaP: Growth and luminescence. <i>Materials Science in Semiconductor Processing</i> , 2001, 4, 497-501.	4.0	22
29	Colour-tunable light-emitting diodes based on InP/GaP nanostructures. <i>Nanotechnology</i> , 2006, 17, 3703-3706.	2.6	22
30	Single-photon emitters based on epitaxial isolated InP/InGaP quantum dots. <i>Applied Physics Letters</i> , 2012, 100, .	3.3	18
31	Self-assembled chains of single layer InP/(In,Ga)P quantum dots on GaAs (001). <i>Journal of Applied Physics</i> , 2009, 105, 124308.	2.5	15
32	Green emission from InP-GaP quantum-dot light-emitting diodes. <i>IEEE Photonics Technology Letters</i> , 2006, 18, 895-897.	2.5	14
33	Optical emission from ultrathin strained type-II InP/GaP quantum wells. <i>Applied Physics Letters</i> , 2001, 79, 2886-2888.	3.3	13
34	Evidence of type-I direct recombination in InP/GaP quantum dots via magnetoluminescence. <i>Applied Physics Letters</i> , 2009, 95, 151105.	3.3	12
35	Controlled growth of InP/In _{0.48} Ga _{0.52} P quantum dots on GaAs substrate. <i>Journal of Crystal Growth</i> , 2011, 323, 228-232.	1.5	12
36	Electrical conductivity tensor of O_3 analyzed by van der Pauw measurements: Inherent anisotropy, off-diagonal element, and the impact of grain boundaries. <i>Physical Review Materials</i> , 2019, 3, .	2.4	12

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37	Comparison of MBE Growth of InSb on Si (001) and GaAs (001). Journal of Electronic Materials, 2008, 37, 1799-1805.	2.2	11
38	Highly polarized self-assembled chains of single layer InP/(In,Ga)P quantum dots. Applied Physics Letters, 2010, 97, 253113.	3.3	11
39	Lattice-engineered Si _{1-x} Gex-buffer on Si(001) for GaP integration. Journal of Applied Physics, 2014, 115, 103501.	2.5	10
40	Photonic crystal cavity-assisted upconversion infrared photodetector. Optics Express, 2015, 23, 12998.	3.4	10
41	Plasma-assisted molecular beam epitaxy of SnO(001) films: Metastability, hole transport properties, Seebeck coefficient, and effective hole mass. Physical Review Materials, 2020, 4, .	2.4	10
42	Mid-infrared luminescence of an InNAsSb ⁺ InAs single quantum well grown by molecular beam epitaxy. Applied Physics Letters, 2006, 89, 121912.	3.3	9
43	Chemical Sensitivity of Luminescent Epitaxial Surface InP Quantum Dots. Journal of Sensor Technology, 2013, 03, 1-5.	1.0	8
44	AlP/GaP distributed Bragg reflectors. Applied Physics Letters, 2013, 103, 031101.	3.3	8
45	Chemical sensitivity of InP/In _{0.48} Ga _{0.52} P surface quantum dots studied by time-resolved photoluminescence spectroscopy. Journal of Luminescence, 2015, 168, 54-58.	3.1	8
46	Precise electron beam-based target-wavelength trimming for frequency conversion in integrated photonic resonators. Optics Express, 2022, 30, 6921.	3.4	8
47	Low frequency noise in InSb/GaAs and InSb/Si channels. Applied Physics Letters, 2010, 97, .	3.3	7
48	Optical Properties of Dilute Nitride InN(As)Sb Quantum Wells and Quantum Dots Grown by Molecular Beam Epitaxy. Journal of Electronic Materials, 2008, 37, 1774-1779.	2.2	6
49	Transport properties of doped AlP for the development of conductive AlP/GaP distributed Bragg reflectors and their integration into light-emitting diodes. Applied Physics Letters, 2018, 112, .	3.3	6
50	Surface InP Quantum Dots: Effect of Morphology on the Photoluminescence Sensitivity. Procedia Engineering, 2012, 47, 1251-1254.	1.2	5
51	Surface InP/In _{0.48} Ga _{0.52} P quantum dots: Carrier recombination dynamics and their interaction with fluorescent dyes. Journal of Applied Physics, 2013, 114, 163510.	2.5	5
52	High Efficient THz Emission From Unbiased and Biased Semiconductor Nanowires Fabricated Using Electron Beam Lithography. IEEE Journal of Selected Topics in Quantum Electronics, 2017, 23, 1-7.	2.9	5
53	Vapour Sensitivity of InP Surface Quantum Dots. Key Engineering Materials, 0, 605, 177-180.	0.4	4
54	Deep-level noise characterization of MOVPE-grown In _{0.48} Ga _{0.52} P-Ga ₂ O ₃ . Applied Physics Letters, 2019, 115, .	3.3	4

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55	Narrow-gap ferromagnetic semiconductors (In,Mn)Sb on GaAs (001): growth and properties. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 1492-1496.	0.8	3
56	Quasiresonant excitation of InP/InGaP quantum dots using second harmonic generated in a photonic crystal cavity. Applied Physics Letters, 2012, 101, .	3.3	3
57	Thermal annealing effect on the structural properties of epitaxial growth of GaP on Si substrate. Journal of Crystal Growth, 2015, 419, 42-46.	1.5	3
58	Thermal behavior and carrier injection of GaAs/GaP quantum dots light emitting diodes. Applied Physics Letters, 2017, 110, .	3.3	3
59	Second harmonic generation in GaP photonic crystal waveguides. , 2011, , .		2
60	Shape induced anisotropic elastic relaxation in InP/In _{0.48} Ga _{0.52} P quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 1139-1142.	2.7	1
61	Recombination dynamics in self-assembled InP/GaP quantum dots under high pressure. Physica Status Solidi (B): Basic Research, 2004, 241, 3263-3268.	1.5	1
62	Optical properties and carrier dynamics of InP quantum dots embedded in GaP. , 2004, , .		1
63	Bio-medical imaging with a terahertz quantum cascade laser. , 2006, , .		1
64	Growth and Characterization of InSb films on Si (001). Materials Research Society Symposia Proceedings, 2008, 1068, 1.	0.1	1
65	Photoluminescence of InP/GaP quantum dots under extreme conditions. High Pressure Research, 2009, 29, 488-494.	1.2	1
66	THz emission from InP and InGaAs nanowires fabricated using electron beam lithography. , 2015, , .		1
67	Room temperature green to red electroluminescence from (Al,Ga)As/GaP QDs and QWs. Proceedings of SPIE, 2016, , .	0.8	1
68	Light-emitting diodes based on InP quantum dots in GaP(100). , 2005, , .		0
69	Investigation of Optical Properties of Nitrogen Incorporated Sb based Quantum Well and Quantum Dots for Infrared Sensors Application. Materials Research Society Symposia Proceedings, 2006, 955, 1.	0.1	0
70	Investigation of Nitrogen Induced closely coupled Sb based Quantum Dots for Infrared Sensors Application. Materials Research Society Symposia Proceedings, 2006, 959, 1.	0.1	0
71	Comparative Analysis of Bio-Medical Imaging at 3.7 Terahertz with a High Power Quantum Cascade Laser. , 2006, , .		0
72	Tunable light sources in the visible and near infrared based on fiber taper coupled photonic crystal nanocavities. , 2010, , .		0

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73	A hybrid quantum photonic interface for solid state qubits. Proceedings of SPIE, 2011, , .	0.8	0
74	Distribution of Mn in ferromagnetic (In,Mn)Sb films grown on (001) GaAs using MBE. Journal of Crystal Growth, 2011, 323, 340-343.	1.5	0
75	A comparison of the low frequency noise in InSb grown on GaAs and Si by MBE. Journal of Crystal Growth, 2011, 323, 393-396.	1.5	0
76	Optical properties of well-isolated single InP/InGaP quantum dots. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 1288-1291.	0.8	0
77	Biased THz emission from InGaAs nanowires fabricated using electron beam lithography. , 2016, , .		0
78	Probing High-Q Photonic Crystal Resonances with Fluorescent Molecules. , 2009, , .		0
79	Second Harmonic Generation in Gallium Phosphide Photonic Crystal Nanocavities with Ultralow CW Pump Power. , 2010, , .		0